

PbFreeProduct

NCE40TH60BP

600V, 40A, Trench FS II Fast IGBT

General Description:

Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 600V Trench FSIIIGBT offers superior conduction and switching performances, and easy parallel operation;

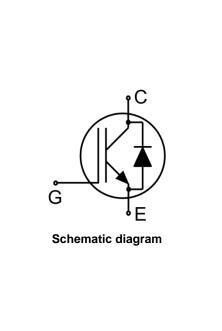
Features

Trench FSII Technology offering

- Very low V_{CE (sat)}
- High speed switching
- Positive temperature coefficient in V_{CE (sat)}
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- Air Condition
- Inverters
- Motor drives



Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE40TH60BP	TO-3P	NCE40TH60BP



TO-3P

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCES	Collector-Emitter Voltage	600	V
V _{GES}	Gate- Emitter Voltage	±30	V
L.	Collector Current	80	A
lc	Collector Current @T _c = 100 °C	40	A
I _{Cplus}	Pulsed Collector Current, t _p limited by T _{jmax}	120	A
-	turn off safe operating area, V _{CE} =600V, Tj=150°C	120	A
lF	Diode Continuous Forward Current @T _c = 100 °C	30	A
IFM	Diode Maximum Forward Current	90	A
D	Power Dissipation @ T _c = 25°C	286	W
Po	Power Dissipation @T _c = 100 °C	114	W
T _J ,T _{stg}	Operating Junction and Storage Temperature Range	-55 to +150	°C
TL	Maximum Temperature for Soldering	260	°C
t _{sc}	Short circuit withstand time V _{GE} =15V, V _{CC} \leq 400V, Allowed number of short circuits<1000Time between short circuits: \geq 1.0s,T _j \leq 150°C	3	us



NCE40TH60BP

Thermal Characteristic

Symbol	Parameter	Value	Units
Rejc	Thermal Resistance, Junction to case for IGBT	0.43	°C/W
Rejc	Thermal Resistance, Junction to case for Diode	2.12	°C/W
Reja	Thermal Resistance, Junction to Ambient	40	°C/W

Electrical Characteristics (Tc=25°C unless otherwise noted)

Currence al	Devementer	Test Conditions		Value			
Symbol	Parameter			Min.	Тур.	Max.	Units
STATIC Cha	racteristics						
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V	,I _{CE} =1mA	600			V
ICES	Collector-Emitter Leakage Current	V _{GE} =0V	V _{CE} =600V			4	uA
IGES(F)	Gate to Emitter Forward Leakage	V _{GE} =+30	V,V _{CE} =0V			200	nA
IGES(R)	Gate to Source Reverse Leakage	V _{GE} =-30	V,V _{CE} =0V			200	nA
	Collector-Emitter Saturation Voltage	Ic=40A	Tj=25°C		1.7	1.9	V
V _{CE(sat)}	Collector-Emitter Saturation voltage	$V_{GE}=15V$	Tj=150°C		1.9		V
$V_{\text{GE(th)}}$	Gate Threshold Voltage	lc=1mA	,Vce=Vge	4.0	5.0	6.0	V
Dynamic Ch	aracteristics						
Cies	Input Capacitance	- V _{CE} =25V,V _{GE} =0V, f=1MHz			4894		pF
Coes	Output Capacitance				136		
Cres	Reverse Transfer Capacitance				94		
Qg	Total Gate Charge				176		
Qge	Gate to Emitter Charge	V _{CC} =480V, I _C =40A V _{GE} =15V			38		nC
Q _{gc}	Gate to Collector Charge				73		
I _{C(SC)}	Short circuit collector current Max.1000 short circuits Time between short circuits: ≥1.0s	V _{GE} =15V,V _{CC} ≪400V, t _{SC} ≪3us,Tj≪150°C			250		A
Switching C	haracteristics						
t _{d(ON)}	Turn-on Delay Time				19		
tr	Rise Time	V _{CC} =400V,Ic=40A V _{GE} =0/15V, R _g =5Ω			17		ns
$t_{\text{d}(\text{OFF})}$	Turn-Off Delay Time				168		
tf	Fall Time				16		
Eon	Turn-On Switching Loss	Inductive Load			0.58		
E _{off}	Turn-Off Switching Loss				0.48		mJ
Ets	Total Switching Loss	1			1.06		

Electrical Characteristics of the Diode (Tc= 25°C unless otherwise specified):

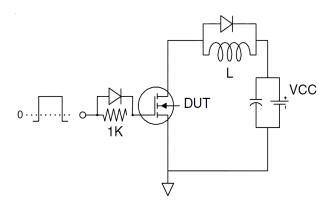
Symbol	Parameter	Toot Conditions	Rating			Units
		Test Conditions	Min.	Тур.	Max.	Units
Vfm	Diode Forward Voltage	IF=30A		1.65	2.0	V
Trr	Reverse Recovery Time			170		ns
IRRM	Diode Peak Reverse Recovery Current	I _F =30A, di/dt=200A/us		6.5		А
Qrr	Reverse Recovery Charge			0.7		uC
Pulse width ttp	≤380μs,δ≤2%	•				



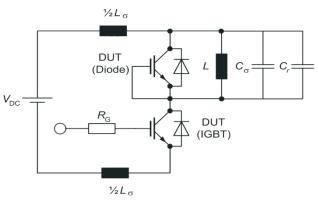


Test Circuit



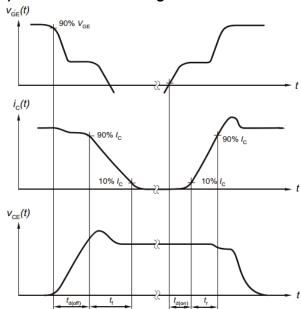


2) Switch Time Test Circuit

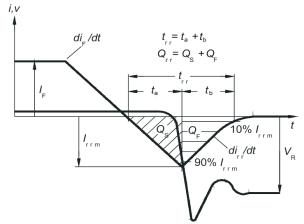


Switching characteristics

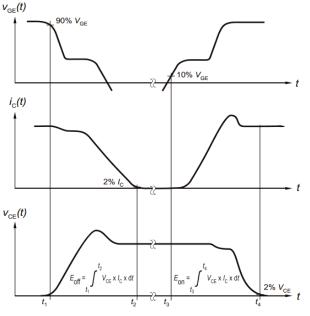
1) definition of switching times



3) Definition of diode switching characteristics



2) definition of switching losses





Typical Electrical and Thermal Characteristics



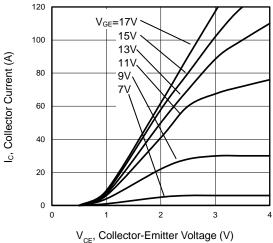


Figure 3 V_{CEsat} vs. Case Temperature

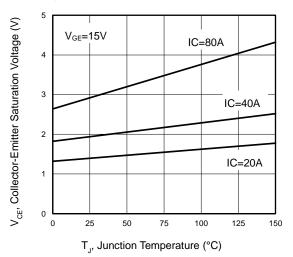
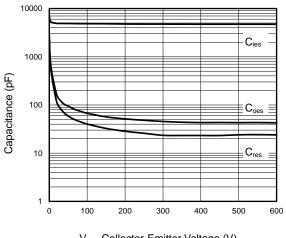


Figure 5 Capacitance Characteristics



V_{CE}, Collector-Emitter Voltage (V)

120 V_{CE}=20V 100 Ic, Collector Current (A) 80 25°C 60 150°C 40 20 0 8 9 10 11 5 V_{GE}, Gate-Emitter Voltage (V)

Figure 4 Saturation Voltage vs. VGE

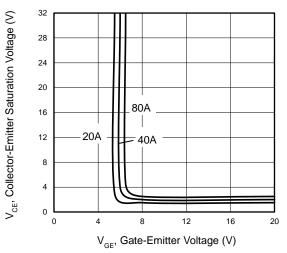


Figure 6 Gate charge waveform

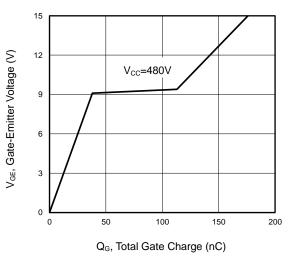


Figure 2 Transfer Characteristics



Typical Electrical and Thermal Characteristics

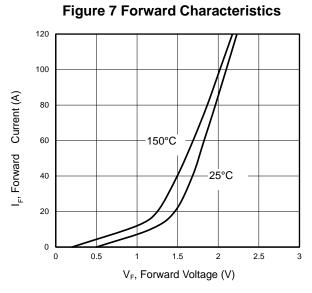


Figure 9 Typical Switching Times as a Function of Gate Resistor

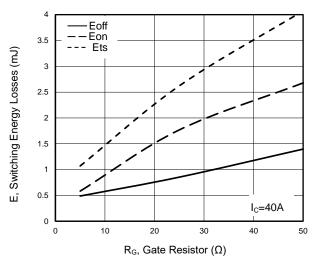
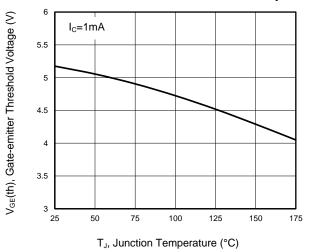
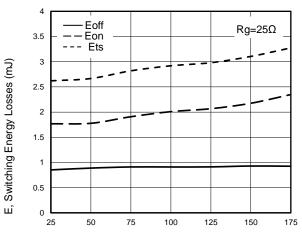


Figure 11 Gate-emitter Threshold Voltage as a Function of Junction Temperature



2 IF=30A 1.5 15A V_F, Forward Voltage (V) 1 8A 0.5 0 25 50 75 100 125 150 175 T_J, Junction Temperature (°C)

Figure 10 Typical Switching Times as a Function of Junction Temperature



 T_J , Junction Temperature (°C)

Figure 12 Typical Collector-emitter Saturation Voltage as a function of Collector Current

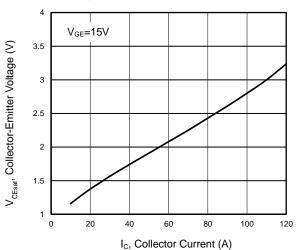


Figure 8 V_F vs. Temperature



Typical Electrical and Thermal Characteristics

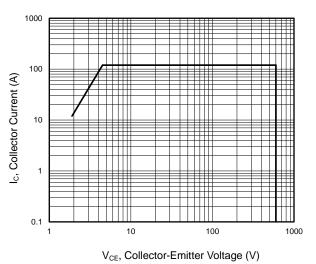
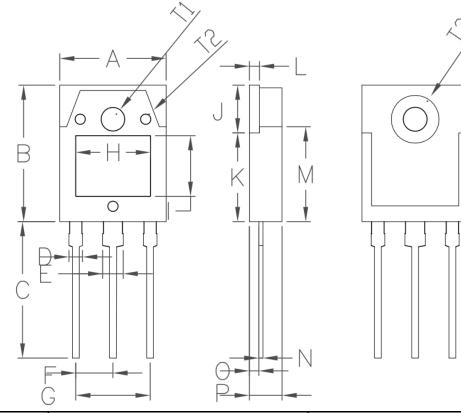


Figure 13 Forward Bias Safe Operating Area



TO-3P-3L Package Information



Cumhal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	15.50	15.70	0.61	0.62	
В	19.70	20.10	0.78	0.79	
С	20.10	20.50	0.79	0.81	
D	2.	00	0.	08	
E	3.	00	0.	12	
F	5.	45	0.	21	
G	10	.90	0.	43	
Н	10.80	11.00	0.43	0.43	
I	8.80	9.00	0.35	0.35	
J	6.85	7.15	0.27	0.28	
К	12.75	13.05	0.50	0.51	
L	1.49	1.51	0.06	0.06	
М	13.70	14.00	0.54	0.55	
N	0.59	0.61	0.02	0.02	
0	1.32	1.48	0.05	0.06	
Р	4.70	4.90	0.19	0.19	
S	4°		0.16°		
T1	3.50		0.14		
T2	1.50		0.06		
Т3	7.00		0.28		





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